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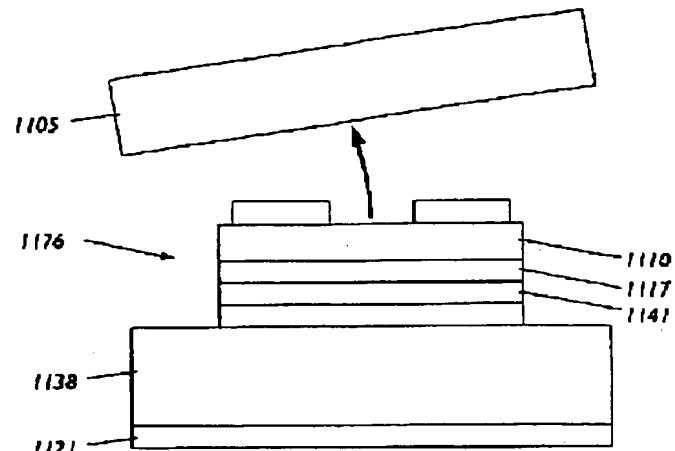
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APPLICANT : XEROX CORP;

INVENTOR : LINDA T ROMANO;

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TITLE : STRUCTURE OF NITRIDE LASER
DIODE WHERE GROWTH SUBSTRATE
IS ELIMINATED AND METHOD FOR
MANUFACTURING NITRIDE DIODE
ARRAY STRUCTURE



ABSTRACT : PROBLEM TO BE SOLVED: To simplify formation of an electrical contact to a laser diode array, avoid the use of special structures, and mount a heat sink to the laser diode array by eliminating a sapphire substrate after laser diode array structure is grown.

SOLUTION: After a semiconductor film with laser diode array structure is grown, a support substrate 1105 is mounted to a side opposite to the side of the sapphire substrate of the semiconductor film. After that, the sapphire substrate is eliminated. After the sapphire substrate has been eliminated, a heat-conductive substrate 1138 is mounted to a side where the sapphire substrate was located. Since the sapphire substrate has been eliminated, no special structure for providing an electrical contact to a laser diode array is required, and a more effective heat sink effect can be obtained.

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